



32V PNP MEDIUM POWER TRANSISTOR IN SOT89

Features

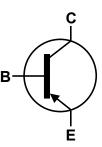
- BV_{CEO} > -32V
- I_C = -2A high Continuous Current
- Low saturation voltage V_{CE(sat)} < 800mV @ 2A
- Complementary NPN Type: 2DD1766
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

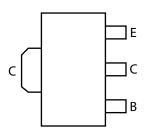
- Case: SOT89
- Case material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.052 grams (approximate)







Device Symbol



Pin Out - Top View

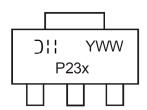
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
2DB1188P-13	P23P	13	12	2,500
2DB1188Q-13	P23Q	13	12	2,500
2DB1188Q-13R	P23Q	13	12	4,000
2DB1188R-13	P23R	13	12	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



P23x = Product Type Marking Code
Where P23P = 2DB1188P

P23Q = 2DB1188Q P23R = 2DB1188R

O'!! = Manufacturers' code marking YWW = Date Code Marking Y = Last Digit of Year (ex: 1 = 2011) WW = Week Code (01 – 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-32	V
Emitter-Base Voltage	V _{EBO}	-6	V
Continuous Collector Current	Ic	-2	A
Peak Pulse Collector Current	Ісм	-3	A
Base Current	I _B	-500	mA

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	1	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Leads (Note 6)	$R_{ heta JL}$	19	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

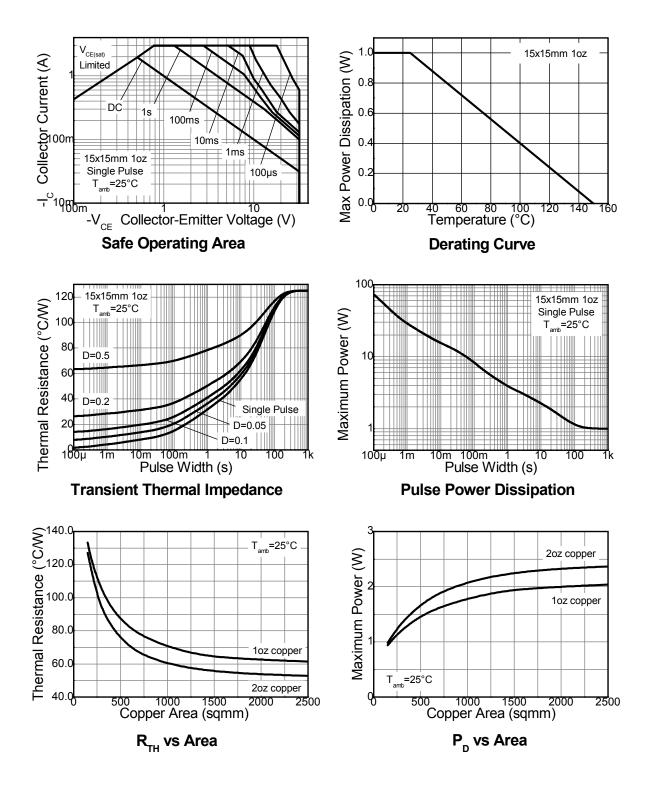
Notes:

^{5.} For a device surface mounted on 15mm x 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Thermal resistance from junction to solder-point (on the exposed collector pad).



Thermal Characteristics and Derating Information

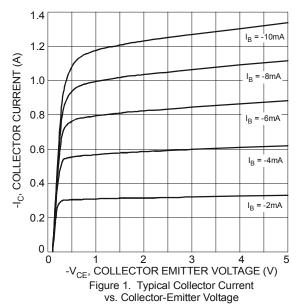




Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Collector-Base Breakdown Voltage		BV _{CBO}	-40	_		V	$I_C = -100\mu A$, $I_E = 0$
Collector-Emitter Breakdown Voltage		BV _{CEO}	-32	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage		BV _{EBO}	-6	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current		I _{CBO}	_	_	-100	nA	$V_{CB} = -20V, I_{E} = 0$
Emitter Cutoff Current		I _{EBO}	_	_	-100	nA	V _{EB} = - 5V, I _C = 0
ON CHARACTERISTICS (Note 7)							
Collector-Emitter Saturation Voltage		V _{CE(sat)}		-0.35	-0.8	V	$I_C = -2A$, $I_B = -0.2A$
DC Current Gain	2DB1188P	h _{FE}	82		180	_	V _{CE} = -3V, I _C = -0.5A
	2DB1188Q		120	_	270		
	2DB1188R		180		390		
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f _T		120		MHz	$V_{CE} = -5V, I_{C} = -0.1A,$ f = 30MHz
Output Capacitance		C _{obo}	_	20	_	pF	V _{CB} = -10V, f = 1MHz

Notes: 7. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



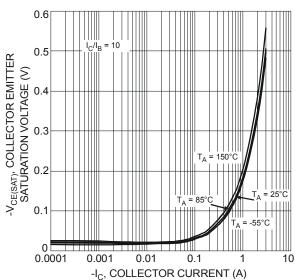


Figure 3. Typical Collector-Emitter Saturation Voltage vs. Collector Current

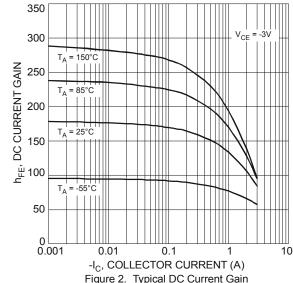


Figure 2. Typical DC Current Gain vs. Collector Current (2DB1188Q)

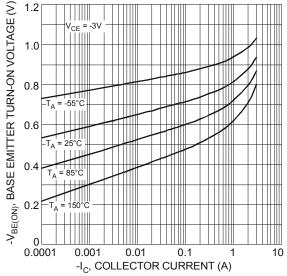
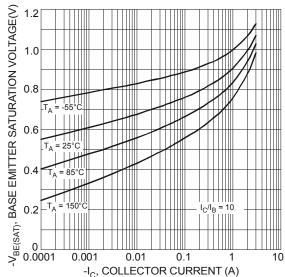


Figure 4. Typical Base-Emitter Turn-On Voltage vs. Collector Current





-I_C, COLLECTOR CURRENT (A)
Figure 5. Typical Base-Emitter Saturation Voltage vs. Collector Current

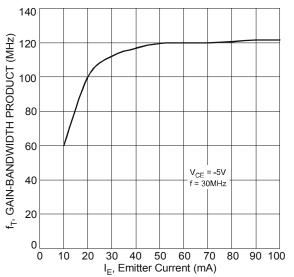


Figure 7. Typical Gain-Bandwidth Product vs. Emitter Current

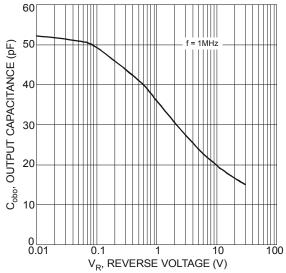
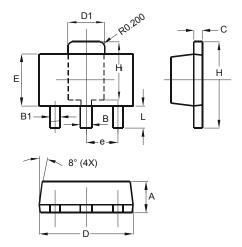


Figure 6. Typical Output Capacitance Characteristics



Package Outline Dimensions

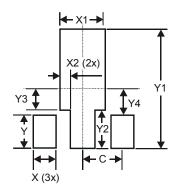
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
Н	3.94	4.25		
H1	2.63	2.93		
L	0.89	1.20		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1 500



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Офис по работе с юридическими лицами:

105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru moschip.ru_6 moschip.ru_4 moschip.ru_9